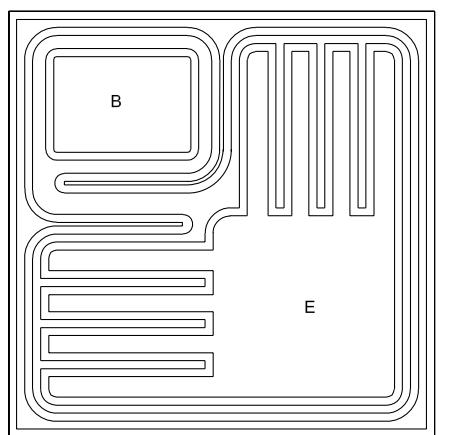


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 X 80 MILS
Die Thickness	8 MILS
Base Bonding Pad Area	18 X 27 MILS
Emitter Bonding Pad Area	34 X 34 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ti/Pd/Ag (20,000Å)

GEOMETRY

BACKSIDE COLLECTOR

R0

GROSS DIE PER 4 INCH WAFER

1,445

PRINCIPAL DEVICE TYPES

CZT122

CJD122

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Hauppauge, NY 11788 USA
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R0 (9 -May 2005)